



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re the Application of

Inventor: Tatau NISHINAGA Group Art Unit: 1722
Appln. No.: 09/511,912 Examiner: M. Anderson
Filed: February 23, 2000
For: A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated June 30, 2005, the Applicant hereby petitions for a two-month extension of time (the fee may be charged to deposit account no. 19-4375) and requests reconsideration and allowance in light of the following remarks.

Claims 7-10 and 19 stand withdrawn.

Claims 1-6, 11-18, and 20-23 stand rejected, under 35 USC §103(a), as being unpatentable over Tanaka et al. (US 6,377,596) in view of Tokunaga et al. (US 5,425,808) and Nakamura et al. (JP 01-234389A). The Applicant respectfully traverses these rejections.

The Office Action proposes that Tokunaga suggests the equivalency of molecular beam epitaxy (MBE) and chemical vapor deposition (CVD) for developing a film via epitaxial lateral overgrowth (ELO) (Office Action page 3, lines 8-16). Although